

RJK6052DPP-M0

Silicon N Channel MOS FET High Speed Power Switching

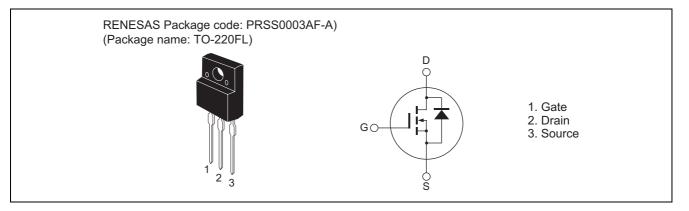
> REJ03G1799-0100 Rev.1.00 Jul 02, 2009

> > $(T_0 - 25^{\circ}C)$

Features

- Low on-resistance
- Low leakage current
- High speed switching

Outline



Absolute Maximum Ratings

			$(1a = 25^{\circ}C)$
Item	Symbol	Ratings	Unit
Drain to source voltage	V _{DSS}	600	V
Gate to source voltage	V _{GSS}	±30	V
Drain current	I _D ^{Note4}	10	А
Drain peak current	I _{D (pulse)} Note1	20	А
Body-drain diode reverse drain current	I _{DR}	10	А
Body-drain diode reverse drain peak current	I _{DR (pulse)} Note1	20	А
Avalanche current	I _{AP} Note3	3	А
Avalanche energy	E _{AR} ^{Note3}	0.49	mJ
Channel dissipation	Pch ^{Note2}	30	W
Channel to case thermal impedance	θch-c	4.17	°C/W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes: 1. $PW \le 10 \ \mu s$, duty cycle $\le 1\%$

2. Value at Tc = 25°C

- 3. STch = 25° C, Tch $\leq 150^{\circ}$ C
- 4. Limited by maximum safe operation area



Electrical Characteristics

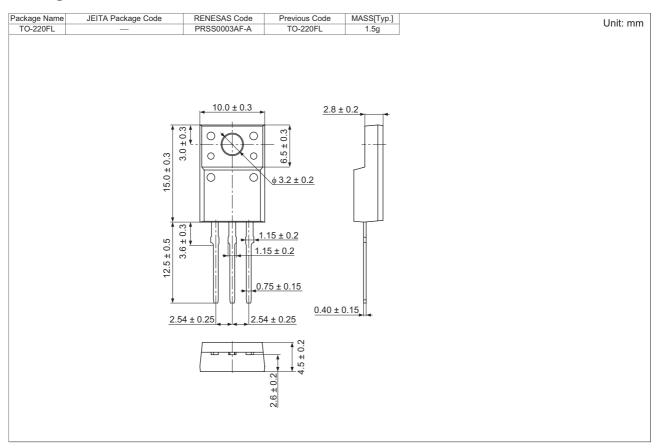
 $(Ta = 25^{\circ}C)$

Item	Symbol	Min	Тур	Мах	Unit	Test conditions
Drain to source breakdown voltage	V _{(BR)DSS}	600			V	$I_D = 10 \text{ mA}, V_{GS} = 0$
Zero gate voltage drain current	I _{DSS}	_	_	1	μA	$V_{DS} = 600 \text{ V}, \text{ V}_{GS} = 0$
Gate to source leak current	I _{GSS}	_		±0.1	μA	$V_{GS} = \pm 30 \text{ V}, \text{ V}_{DS} = 0$
Gate to source cutoff voltage	V _{GS(off)}	3.0		4.5	V	$V_{DS} = 10 \text{ V}, \text{ I}_{D} = 1 \text{ mA}$
Static drain to source on state	R _{DS(on)}	_	0.77	1.07	Ω	$I_D = 5 \text{ A}, V_{GS} = 10 \text{ V}^{Note5}$
resistance						
Input capacitance	Ciss	—	1070	_	pF	V _{DS} = 25 V
Output capacitance	Coss	_	110		pF	V _{GS} = 0 f = 1 MHz
Reverse transfer capacitance	Crss	_	14	_	pF	
Turn-on delay time	t _{d(on)}	_	30	—	ns	I _D = 5 A
Rise time	tr	_	19	_	ns	$V_{GS} = 10 V$ $R_L = 60 \Omega$ $Rg = 10 \Omega$
Turn-off delay time	t _{d(off)}	_	72	_	ns	
Fall time	t _f		15	—	ns	
Total gate charge	Qg	_	29.6	_	nC	V _{DD} = 480 V
Gate to source charge	Qgs	_	5.4	_	nC	V _{GS} = 10 V I _D = 10 A
Gate to drain charge	Qgd	_	13.7	_	nC	
Body-drain diode forward voltage	V _{DF}	_	0.88	1.50	V	$I_F = 10 \text{ A}, V_{GS} = 0^{\text{Note5}}$
Body-drain diode reverse recovery time	t _{rr}	—	280	—	ns	$I_F = 10 \text{ A}, V_{GS} = 0$
						di _F /dt = 100 A/µs

Notes: 5. Pulse test



Package Dimension



Ordering Information

Part No.	Quantity	Shipping Container
RJK6052DPP-M0-T2	1050 pcs	Box (Tube)



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